## TAIWAN SEMICONDUCTOR

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# 25A, 35V - 150V Schottky Barrier Rectifier

### **FEATURES**

- AEC-Q101 qualified available
- Low power loss, high efficiency
- Guard ring for overvoltage protection
- High surge current capability
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

## **APPLICATIONS**

- Switching mode power supply (SMPS)
- Adapters
- DC to DC converters

## **MECHANICAL DATA**

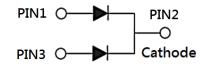
- Case: TO-220AB
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Mounting torque: 0.56 N·m maximum
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 1.90g (approximately)

KEY PARAMETERS			
PARAMETER	VALUE	UNIT	
I <sub>F</sub>	25	А	
V <sub>RRM</sub>	35 - 150	V	
I <sub>FSM</sub>	200	А	
T <sub>J MAX</sub>	150	°C	
Package	TO-220AB		
Configuration	Dual dies		





TO-220AB



<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_A = 25^{\circ}C$ unless otherwise noted)									
		MBR	MBR	MBR	MBR	MBR	MBR	MBR	
PARAMETER	SYMBOL	2535	2545	2550	2560	2590	25100	25150	UNIT
		СТ	СТ	СТ	СТ	СТ	СТ	СТ	
Marking code on the device		MBR 2535 CT	MBR 2545 CT	MBR 2550 CT	MBR 2560 CT	MBR 2590 CT	MBR 25100 CT	MBR 25150 CT	
Repetitive peak reverse voltage	V <sub>RRM</sub>	35	45	50	60	90	100	150	V
Reverse voltage, total rms value	V <sub>R(RMS)</sub>	24	31	35	42	63	70	105	V
Forward current	I <sub>F</sub>				25				Α
Surge peak forward current, 8.3ms single half sine wave superimposed on rated load	I <sub>FSM</sub>	л 200		A					
Peak repetitive reverse surge current <sup>(1)</sup>	I <sub>RRM</sub>	1 0.5		Α					
Peak repetitive forward current (Rated V <sub>R</sub> , Square wave, 20KHz)	I <sub>FRM</sub>				25				А
Critical rate of rise of off-state voltage	dv/dt	dv/dt 10,000		V/µs					
Junction temperature	TJ			-	55 to +	150			°C
Storage temperature	T <sub>STG</sub>			-	55 to +	150			°C

Notes:

1. tp = 2.0µs, 1.0KHz



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THERMAL PERFORMANCE			
PARAMETER	SYMBOL	ТҮР	UNIT
Junction-to-case thermal resistance	R <sub>eJC</sub>	1	°C/W

ELECTRICAL SPECIFICATIONS ( $T_A = 25^{\circ}C$ unless otherwise noted)						
PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
	MBR2535CT MBR2545CT MBR2550CT MBR2560CT			-	- 0.75	V V
	MBR2590CT MBR25100CT			-	0.85	V
	MBR25150CT			-	0.95	V
	MBR2535CT MBR2545CT			-	0.82	V
	MBR2550CT MBR2560CT	I <sub>F</sub> = 25.0A, T <sub>J</sub> = 25°C		-	-	V
	MBR2590CT MBR25100CT			-	0.92	V
Forward voltage per	MBR25150CT		\/_	-	1.02	V
diode <sup>(1)</sup>	MBR2535CT MBR2545CT		V <sub>F</sub>	-	-	V
	MBR2550CT MBR2560CT			-	0.65	V
	MBR2590CT MBR25100CT			-	0.75	V
	MBR25150CT			-	0.92	V
	MBR2535CT MBR2545CT	I <sub>F</sub> = 25.0A, T <sub>J</sub> = 125°C		-	0.73	V
	MBR2550CT MBR2560CT			-	-	V
	MBR2590CT MBR25100CT			-	0.88	V
	MBR25150CT			-	0.98	V
	MBR2535CT MBR2545CT MBR2550CT MBR2560CT	T <sub>J</sub> =25°C	I <sub>R</sub>	-	200	μΑ
	MBR2590CT MBR25100CT MBR25150CT			-	100	μΑ
	MBR2535CT MBR2545CT	T <sub>J</sub> = 125°C		-	15	mA
	MBR2550CT MBR2560CT			-	10	mA
	MBR2590CT MBR25100CT			-	7.5	mA
	MBR25150CT			-	5	mA

#### Notes:

1. Pulse test with PW = 0.3ms

2. Pulse test with PW = 30ms



# **MBR2535CT – MBR25150CT**

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# ORDERING INFORMATION

ORDERING CODE <sup>(1)(2)</sup>	PACKAGE	PACKING
MBR25xCT	TO-220AB	50 / Tube
MBR25xCTH	TO-220AB	50 / Tube

Notes:

1. "x" defines voltage from 35V(MBR2535CT) to 150V(MBR25150CT)

2. "H" means AEC-Q101 qualified



1000

100

10

1

0.1

0.01

10 20 30

INSTANTANEOUS REVERSE CURRENT (mA)

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**Fig.2 Typical Junction Capacitance** 

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## **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

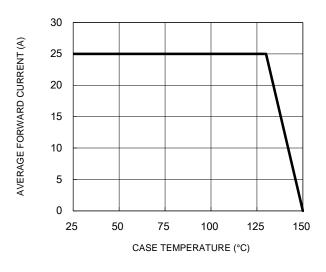


Fig.1 Forward Current Derating Curve

#### **Fig.3 Typical Reverse Characteristics**

T\_=125°C

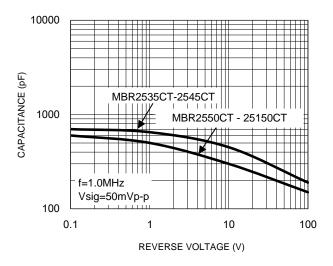
T\_=25°C

50 60 70

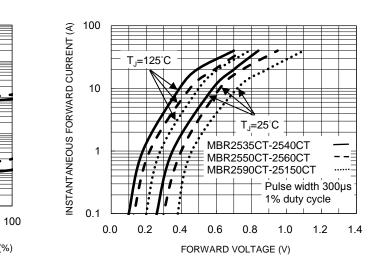
PERCENT OF RATED PEAK REVERSE VOLTAGE (%)

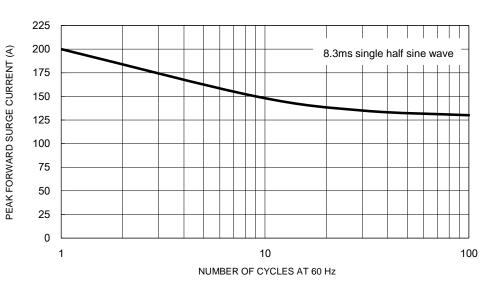
40

MBR2535CT-2545CT MBR2550CT-25150CT



#### **Fig.4 Typical Forward Characteristics**





# Fig.5 Maximum Non-Repetitive Forward Surge Current

90

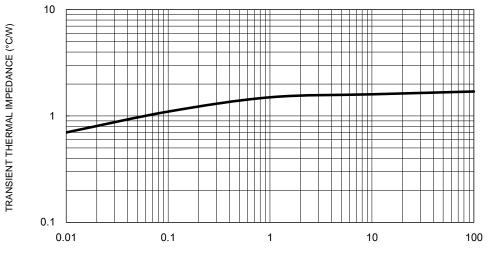
80



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## **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 



#### Fig.6 Typical Transient Thermal Impedance

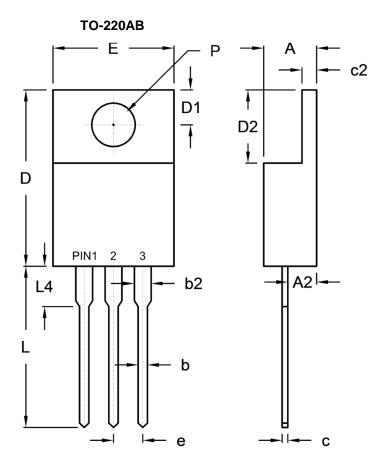
PULSE DURATION (s)



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# **PACKAGE OUTLINE DIMENSIONS**



DIM.	Unit (mm)		Unit	(inch)	
	Min.	Max.	Min.	Max.	
A	4.42	4.76	0.174	0.187	
A2	2.20	2.80	0.087	0.110	
b	0.68	0.94	0.027	0.037	
b2	1.14	1.77	0.045	0.070	
с	0.35	0.64	0.014	0.025	
c2	1.14	1.40	0.045	0.055	
D	14.60	16.00	0.575	0.630	
D1	2.62	3.44	0.103	0.135	
D2	5.84	6.86	0.230	0.270	
E	-	10.50	-	0.413	
е	2.41	2.67	0.095	0.105	
L	13.19	14.79	0.519	0.582	
L4	2.80	4.20	0.110	0.165	
Р	3.54	4.00	0.139	0.157	

## **MARKING DIAGRAM**



P/N	= Marking Code
G	= Green Compound
YWW	= Date Code
F	= Factory Code



# MBR2535CT - MBR25150CT

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